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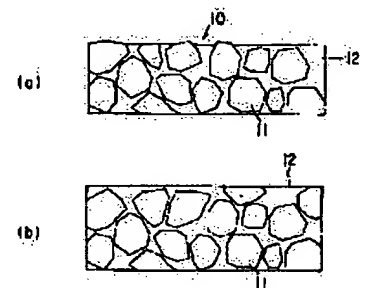
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(54) SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME

(57)Abstract:

PROBLEM TO BE SOLVED: To improve the insulating performance of an insulating film.

SOLUTION: An insulating film 10, formed on the main face side of a semiconductor substrate, is constituted of plural grain-shaped insulating regions 11 made of metallic oxide and an inter-grain insulating region 12 made of amorphous insulating insulators formed among the adjacent grain-shaped insulating regions.



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